

CMLDM5757
SURFACE MOUNT SILICON
DUAL P-CHANNEL
ENHANCEMENT-MODE
MOSFET



www.centrasemi.com



SOT-563 CASE

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMLDM5757 consists of dual silicon P-Channel enhancement-mode MOSFETs designed for high speed pulsed amplifier and driver applications. These MOSFETs offer very low $r_{DS(ON)}$ and low threshold voltage.

MARKING CODE: 77C

FEATURES:

- ESD protection up to 1800V (Human Body Model)
- 350mW power dissipation
- Very low $r_{DS(ON)}$
- Low threshold voltage
- Logic level compatible
- Small, SOT-563 surface mount package
- Complementary dual N-Channel device: CMLDM3737

APPLICATIONS:

- Load switch/Level shifting
- Battery charging
- Boost switch
- Electro-luminescent backlighting

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Drain-Source Voltage	
Gate-Source Voltage	
Continuous Drain Current (Steady State)	
Maximum Pulsed Drain Current ($t_p=10\mu\text{s}$)	
Power Dissipation (Note 1)	
Power Dissipation (Note 2)	
Power Dissipation (Note 3)	
Operating and Storage Junction Temperature	
Thermal Resistance (Note 1)	

SYMBOL

SYMBOL		UNITS
V_{DS}	20	V
V_{GS}	8.0	V
I_D	430	mA
I_{DM}	750	mA
P_D	350	mW
P_D	300	mW
P_D	150	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	357	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS PER TRANSISTOR: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{GSSF}, I_{GSSR}	$V_{GS}=4.5\text{V}, V_{DS}=0$		2.0	μA
I_{DSS}	$V_{DS}=16\text{V}, V_{GS}=0$		1.0	μA
BV_{DSS}	$V_{GS}=0, I_D=250\mu\text{A}$	20		V
$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu\text{A}$	0.45	1.0	V
V_{SD}	$V_{GS}=0, I_S=350\text{mA}$		1.2	V
$r_{DS(ON)}$	$V_{GS}=4.5\text{V}, I_D=430\text{mA}$		0.9	Ω
$r_{DS(ON)}$	$V_{GS}=2.5\text{V}, I_D=300\text{mA}$		1.2	Ω
$r_{DS(ON)}$	$V_{GS}=1.8\text{V}, I_D=150\text{mA}$		2.0	Ω
C_{rss}	$V_{DS}=16\text{V}, V_{GS}=0, f=1.0\text{MHz}$		20	pF
C_{iss}	$V_{DS}=16\text{V}, V_{GS}=0, f=1.0\text{MHz}$		175	pF
C_{oss}	$V_{DS}=16\text{V}, V_{GS}=0, f=1.0\text{MHz}$		30	pF

Notes: (1) Ceramic or aluminum core PC Board with copper mounting pad area of 4.0mm²
(2) FR-4 Epoxy PC Board with copper mounting pad area of 4.0mm²
(3) FR-4 Epoxy PC Board with copper mounting pad area of 1.4mm²

R4 (8-June 2015)

CMLDM5757

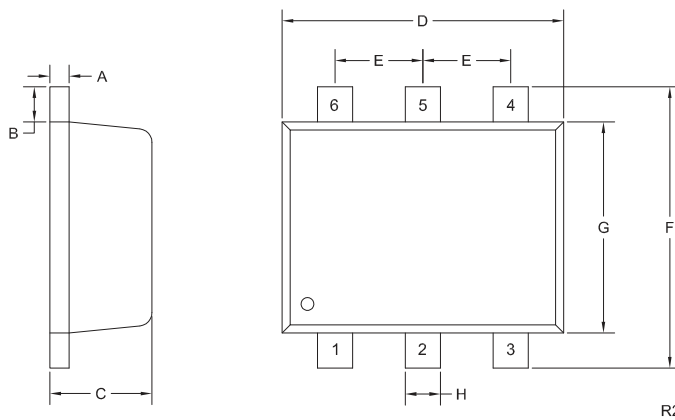
**SURFACE MOUNT SILICON
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ELECTRICAL CHARACTERISTICS PER TRANSISTOR - Continued: ($T_A=25^\circ\text{C}$)

SYMBOL	TEST CONDITIONS	TYP	NITS
$Q_{g(\text{tot})}$	$V_{DS}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=200\text{mA}$	1.2	nC
Q_{gs}	$V_{DS}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=200\text{mA}$	0.24	nC
Q_{gd}	$V_{DS}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=200\text{mA}$	0.36	nC
t_{on}	$V_{DD}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=215\text{mA}$, $R_G=10\Omega$	38	ns
t_{off}	$V_{DD}=10\text{V}$, $V_{GS}=4.5\text{V}$, $I_D=215\text{mA}$, $R_G=10\Omega$	48	ns

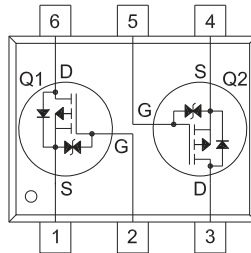
SOT-563 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.0027	0.007	0.07	0.18
B	0.008		0.20	
C	0.017	0.024	0.45	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.059	0.067	1.50	1.70
G	0.043	0.051	1.10	1.30
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R2)

PIN CONFIGURATION



LEAD CODE:

- 1) Source Q1
- 2) Gate Q1
- 3) Drain Q2
- 4) Source Q2
- 5) Gate Q2
- 6) Drain Q1

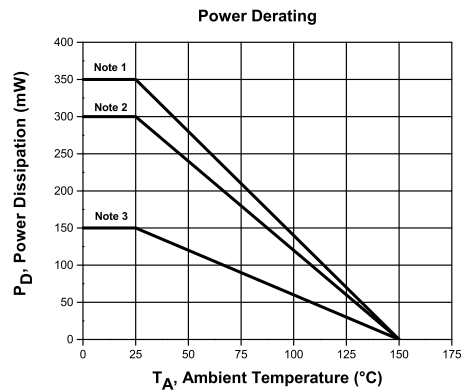
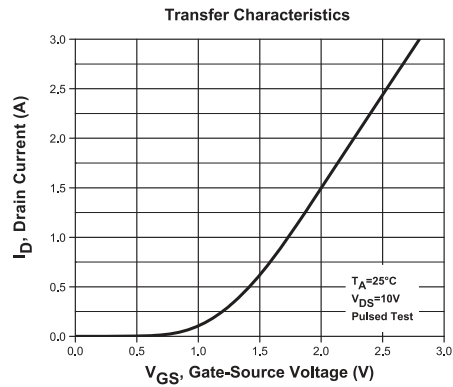
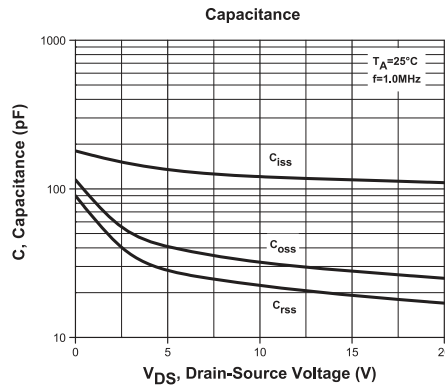
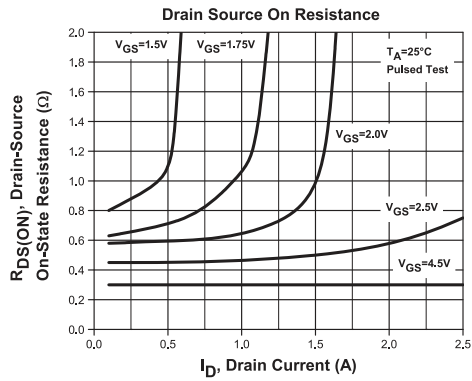
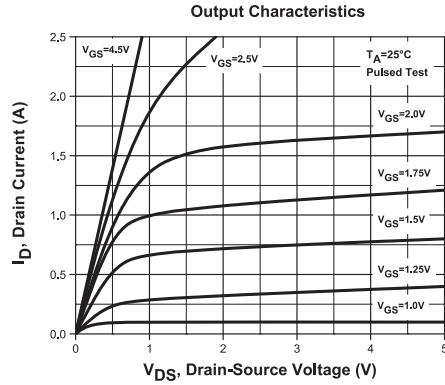
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TYPICAL ELECTRICAL CHARACTERISTICS



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OUTSTANDING SUPPORT AND SUPERIOR SERVICES



PRODUCT SUPPORT

Central's operations team provides the highest level of support to insure product is delivered on-time.

- Supply management (Customer portals)
- Inventory bonding
- Consolidated shipping options
- Custom bar coding for shipments
- Custom product packing

DESIGNER SUPPORT/SERVICES

Central's applications engineering team is ready to discuss your design challenges. Just ask.

- Free quick ship samples (2nd day air)
- Online technical data and parametric search
- SPICE models
- Custom electrical curves
- Environmental regulation compliance
- Customer specific screening
- Up-screening capabilities
- Special wafer diffusions
- PbSn plating options
- Package details
- Application notes
- Application and design sample kits
- Custom product and package development

REQUESTING PRODUCT PLATING

1. If requesting Tin/Lead plated devices, add the suffix "TIN/LEAD" to the part number when ordering (example: 2N2222A TIN/LEAD).
2. If requesting Lead (Pb) Free plated devices, add the suffix "PBFREE" to the part number when ordering (example: 2N2222A PBFREE).

CONTACT US

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